

DFD05T

**Diffused Junction Type Silicon Diode** 

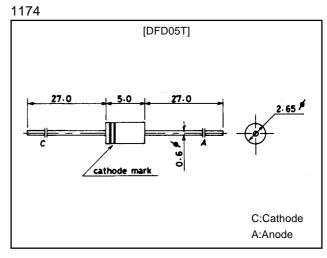
# **0.5A Power Rectifier**

### Features

- · High-speed switching use.
- · Plastic molded structure.
- Reverse recovery time trr=0.15µs max (B, C, E, G). trr=0.3µs max (J, L, N, R, T).
- Peak reverse voltage:  $V_{RM}$ =100 to 1700V
- · Average rectified current  $I_0=0.5A$

### **Package Dimensions**

unit:mm



## **Specifications**

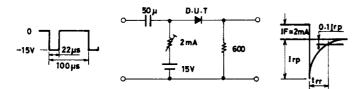
### Absolute Maximum Ratings at Ta = 25 C

Parameter	Symbol	Conditions		DF	DFD05TB		D05TC	DFD05TE	DFD05TG	Unit
Peak Reverse Voltage	V <sub>RM</sub>				100		200	400	600	V
Average Recitified Current	IO	Ta=50°C			$\rightarrow$		$\rightarrow$	$\rightarrow$	0.5	А
Surge Forward Current	IFSM	50Hz sine wave, 1cycle			$\rightarrow$		$\rightarrow$	$\rightarrow$	30	А
Junction Temperature	Tj				$\rightarrow$		$\rightarrow$	$\rightarrow$	150	°C
Storage Temperature	Tstg				$\rightarrow$		$\rightarrow$	$\rightarrow$	-40 to +150	°C
Parameter	Symbol	Conditions	DFD0	5TJ	DFD05T	rl C	OFD05TN	DFD05TR	DFD05TT	Unit
Peak Reverse Voltage	V <sub>RM</sub>			800	10	00	1200	1500	1700	V
Average Recitified Current	IO	Ta=50°C		$\rightarrow$		$\rightarrow$	$\rightarrow$	$\rightarrow$	0.5	А
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	$\rightarrow$			$\rightarrow$	$\rightarrow$	$\rightarrow$	20	A
Junction Temperature	Tj			$\rightarrow$		$\rightarrow$	$\rightarrow$	$\rightarrow$	125	°C
Storage Temperature	Tstg			$\rightarrow$		$\rightarrow$	$\rightarrow$	$\rightarrow$	-40 to +150	°C

### Electrical Characteristics at Ta = 25 C

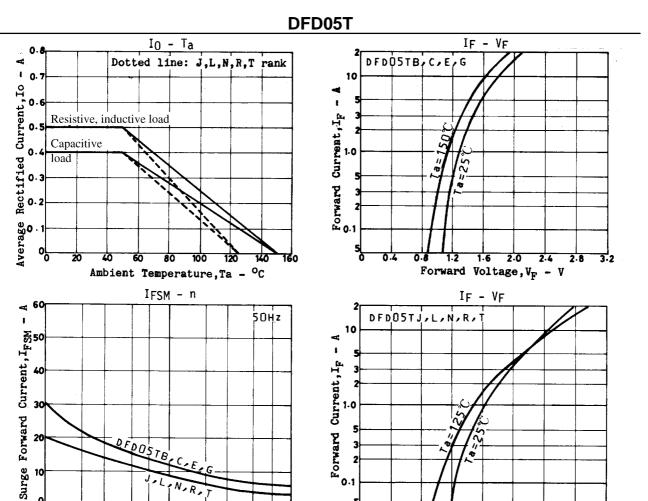
Parameter	Symbol	Conditions		Ratings			
Farameter	Symbol	Conditions	min	typ	max	Unit	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =0.5A (B, C, E, G)			1.2	V	
		I <sub>F</sub> =0.5A (J, L, N, R, T)			1.5	V	
Reverse Current	I <sub>R</sub>	V <sub>R</sub> :At each V <sub>RM</sub>			10	μΑ	
Reverse Recovery Time	trr	I <sub>F</sub> =2mA, V <sub>R</sub> =15V (B,C, E, G)			0.15	μs	
		I <sub>F</sub> =2mA, VR=15V (J, L, N, R, T)			0.3	μs	

#### **Reverse Recovery Time Test Circuit**



Unit (resistance:Ω, capacitance:F)

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100

0.4

0.6

1.2

1.6

Forward Voltage, VF - V

2.0

2.4

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Anyone purchasing any products described or contained herein for an above-mentioned use shall:

R

10

Number of Cycles at 50Hz,n

0 1.0

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